

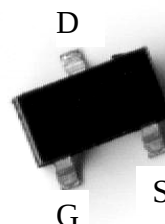
30V N-CHANNEL Enhancement Mode MOSFET

Features:

- Simple drive requirement
- Small package outline
- Pb-free package

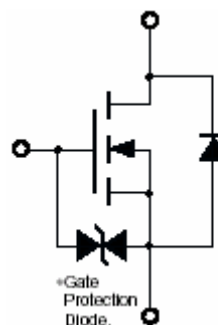
Outline

SOT-23



Symbol

KWN4003N3



G : Gate
S : Source
D : Drain

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @ T _A =25°C, V _{GS} =4V	I _D	1.3	A
Continuous Drain Current @ T _A =70°C, V _{GS} =4V		1.0	
Pulsed Drain Current (Notes 1, 2)	I _{DM}	3	
Maximum Power Dissipation@ T _A =25°C	P _D	1.38 (Note 3)	W
Linear Derating Factor		0.01	W/°C
ESD susceptibility		1000 (Note 4)	V
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C

Note : 1. Pulse width limited by maximum junction temperature.
2. Pulse width ≤ 300μs, duty cycle ≤ 2%.
3. Surface mounted on 1 in² copper pad of FR-4 board, t ≤ 5s.
4. Human body model, 1.5kΩ in series with 100pF.

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient(PCB mounted)	Rth,ja	90	°C/W

Note : Surface mounted on 1 in² copper pad of FR-4 board, t≤5s; 270°C/W when mounted on minimum copper pad.

Electrical Characteristics (Tj=25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	30	-	-	V	V _{GS} =0, I _D =250μA
V _{GS(th)}	1.0	1.3	1.8	V	V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±10	μA	V _{GS} =±20V, V _{DS} =0
I _{DSS}	-	-	1		V _{DS} =30V, V _{GS} =0
	-	-	10		V _{DS} =24V, V _{GS} =0 (T _j =70°C)
*R _{DS(ON)}	-	305	450	mΩ	V _{GS} =10V, I _D =500mA
	-	450	600		V _{GS} =4V, I _D =100mA
	-	810	1000		V _{GS} =2.5V, I _D =100mA
*G _{FS}	-	435	-	mS	V _{DS} =10V, I _D =100mA
Dynamic					
C _{iss}	-	43	-	pF	V _{DS} =5V, V _{GS} =0, f=1MHz
C _{oss}	-	13	-		
C _{rss}	-	8	-		
t _{d(ON)}	-	22	-	ns	V _{DS} =5V, I _D =100mA, V _{GS} =4.5V, R _G =50Ω
t _r	-	26	-		
t _{d(OFF)}	-	72	-		
t _f	-	55	-		
Q _g	-	1.34	-	nC	V _{DS} =24V, I _D =100mA, V _{GS} =5V
Q _{gs}	-	0.1	-		
Q _{gd}	-	0.57	-		
Source-Drain Diode					
*V _{SD}	-	0.74	1.2	V	V _{GS} =0V, I _S =100mA

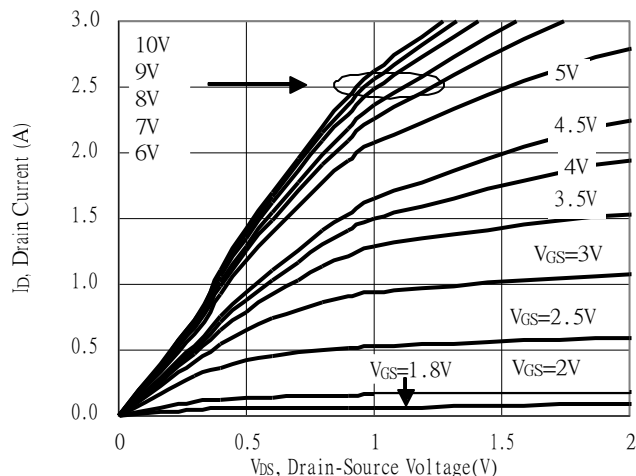
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Ordering Information

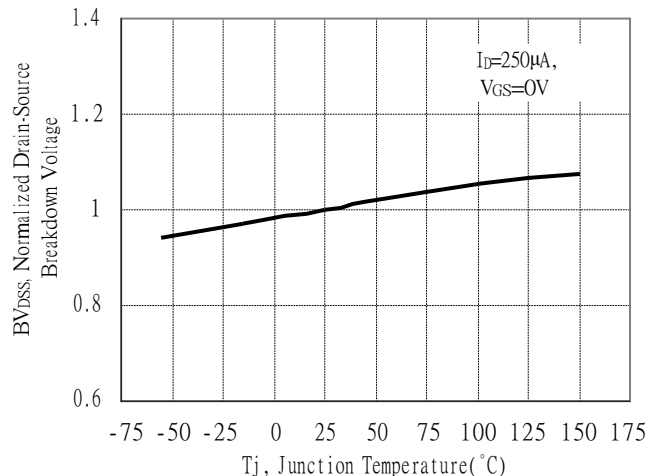
Device	Package	Shipping	Marking
KWN4003N3	SOT-23 (Pb-free)	3000 pcs / Tape & Reel	4003

Typical Characteristics

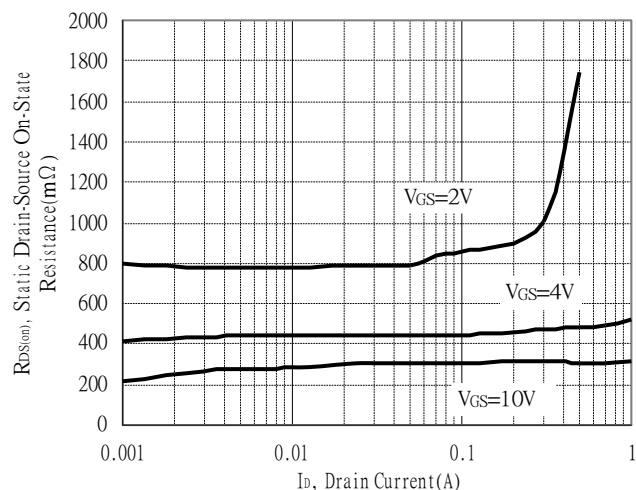
Typical Output Characteristics



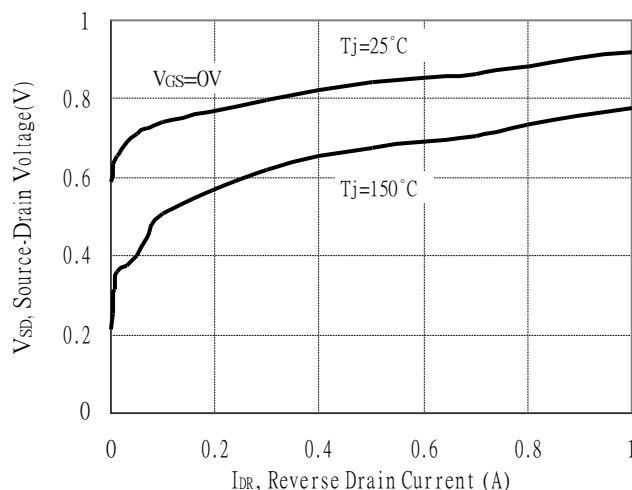
Breakdown Voltage vs Ambient Temperature



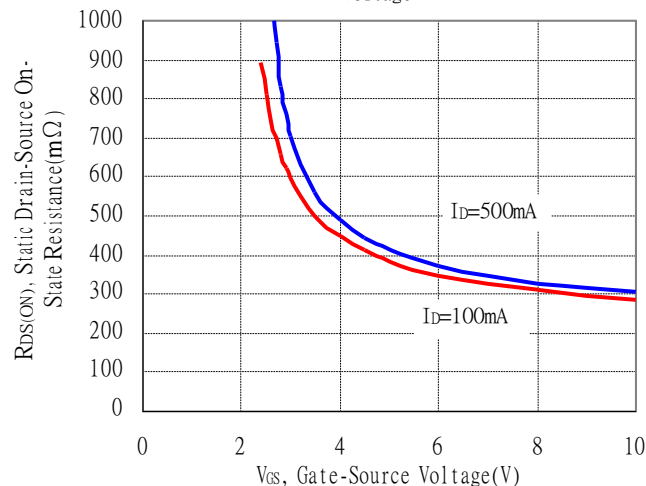
Static Drain-Source On-State resistance vs Drain Current



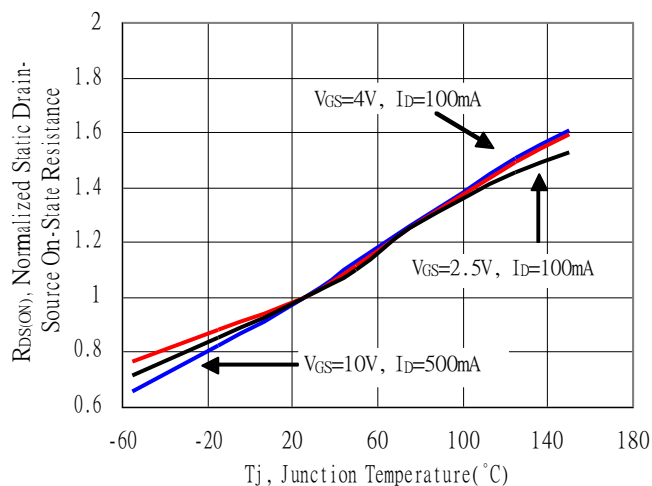
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

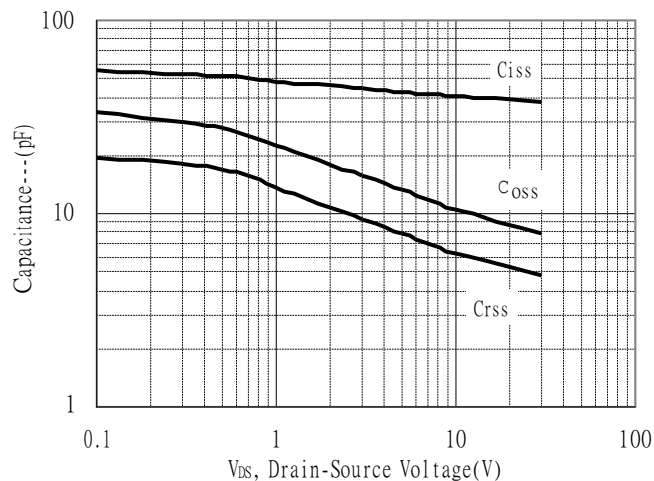


Drain-Source On-State Resistance vs Junction Temperature

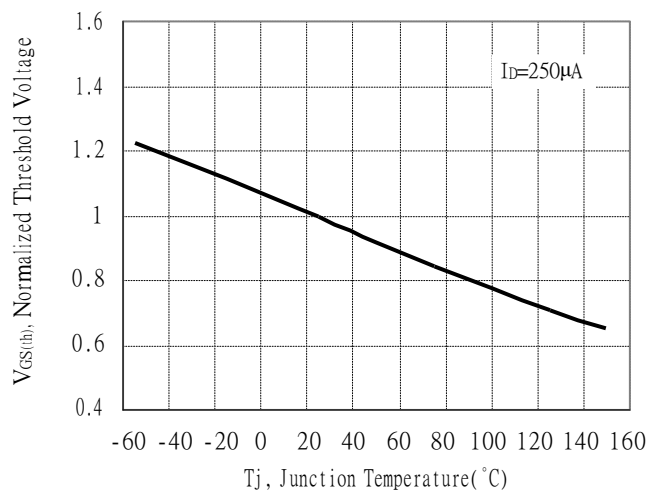


Typical Characteristics(Cont.)

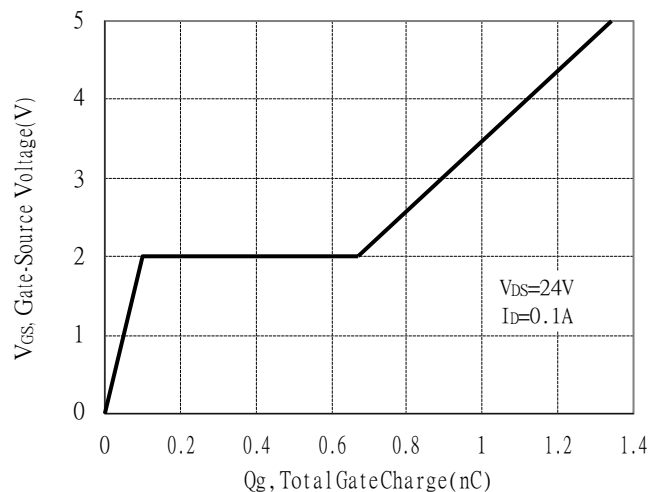
Capacitance vs Drain-to-Source Voltage



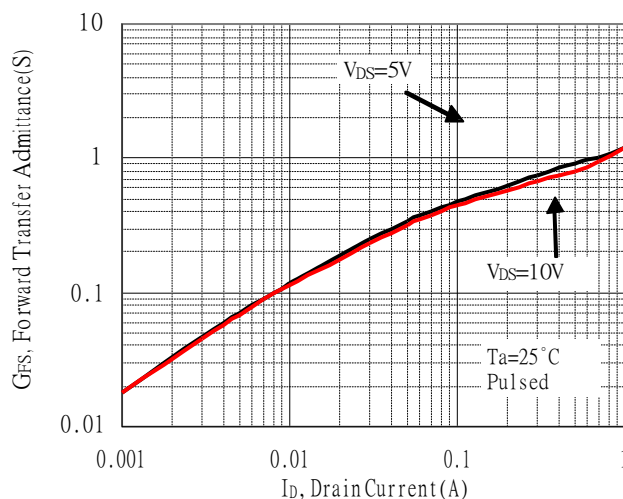
Threshold Voltage vs Junction Temperature



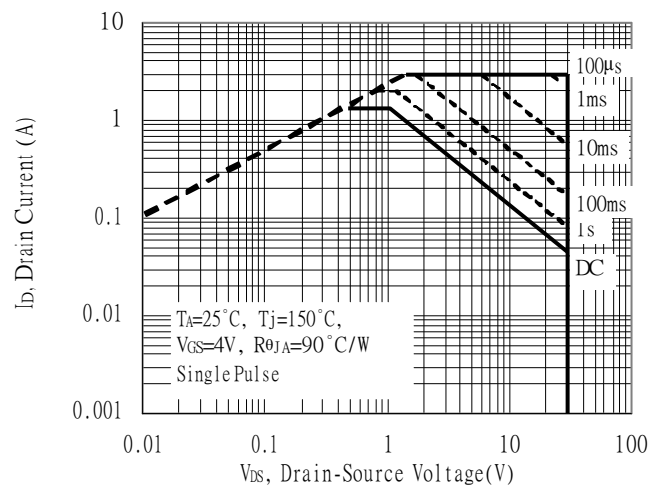
Gate Charge Characteristics



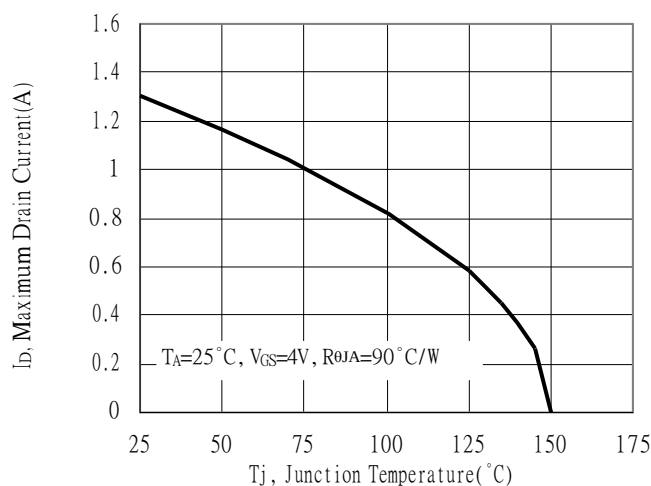
Forward Transfer Admittance vs Drain Current



Maximum Safe Operating Area

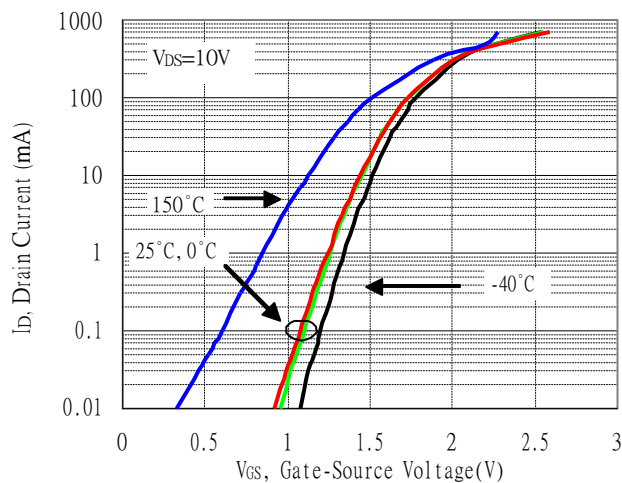


Maximum Drain Current vs Junction Temperature

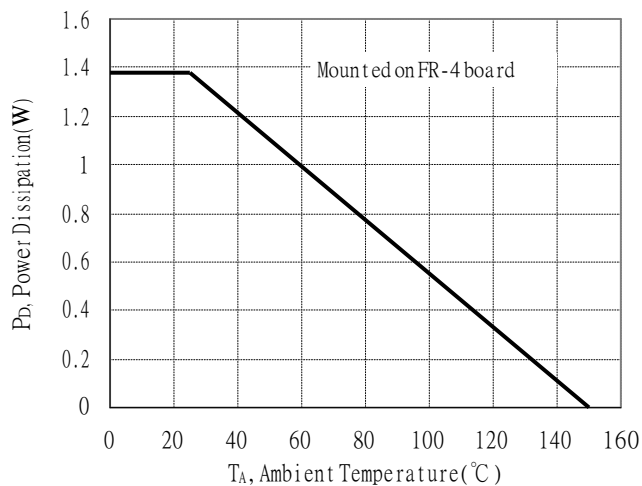


Typical Characteristics(Cont.)

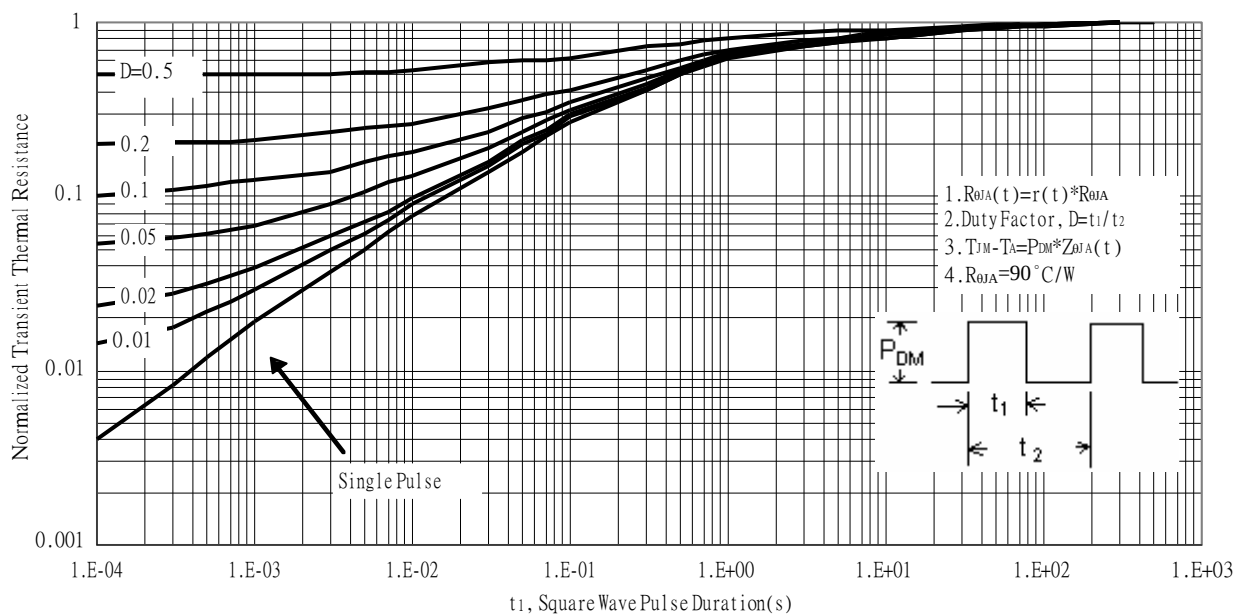
Typical Transfer Characteristics



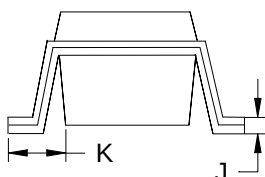
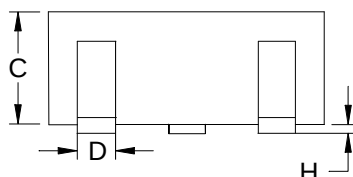
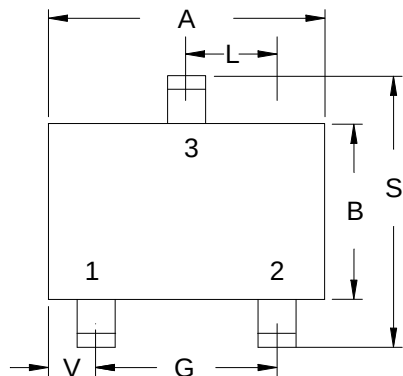
Power Derating Curve



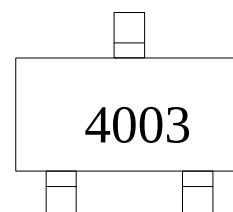
Transient Thermal Response Curves



SOT-23 Dimension



Marking:



3-Lead SOT-23 Plastic
 Surface Mounted Package
 Code: N3

Style: Pin 1.Gate 2.Source 3.Drain

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0669	1.20	1.70	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10					